imall

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A Product Line of Diodes Incorporated



DDR BUS TERMINATION REGULATOR

Description

The AP2303 is a low dropout linear regulator to generate termination voltage of DDR-SDRAM system. The regulator can source or sink up to 1.75A current continuously. The output voltage is regulated to track tightly with the reference voltage ($1/2V_{DDQ}$) within ±10mV.

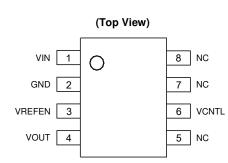
The AP2303 supports soft start-up when used to turn on the VCNTL and VREFEN. It integrates a shutdown circuit that will be triggered once the voltage of VIN, VCNTL or VREFEN falls below a certain value.

AP2303 features over temperature protection and current limit protection for both source and sink.

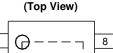
AP2303 is available in packages of SOIC-8 and PSOP-8.

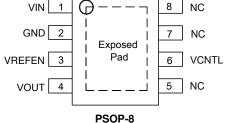
Features

- Support DDR-II (V_{TT}=0.9V), DDR-III (V_{TT}=0.75V), DDR-IIIL (V_{TT}=0.675V), DDR-IV (V_{TT}=0.6V) Application
- Source and Sink up to 1.75A Current
- Output Voltage Accuracy Over Full Load: ±2% (Max.)
- Soft Start-up and Shutdown along with V_{IN}, V_{CNTL} and V_{REFEN} Rising and Shutdown along with V_{IN}, V_{CNTL} and V_{REFEN} Dropping
- Flexible Output by 2 External Resistors
- Requires Minimum 10μF Output Ceramic Capacitor for Application
- Current Limit Protection for Both Source and Sink
- OTSD Protection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)









Applications

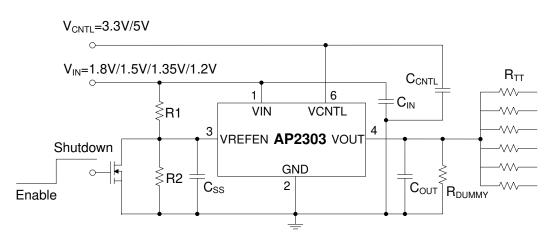
- DDR-II/DDR-III/DDR-IIIL/DDR-IV Memory System
- Desktop PC, Notebook Mother Board
- Graphic Card
- STB, LCD-TV, Web-TV

Pin Assignments

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Typical Applications Circuit



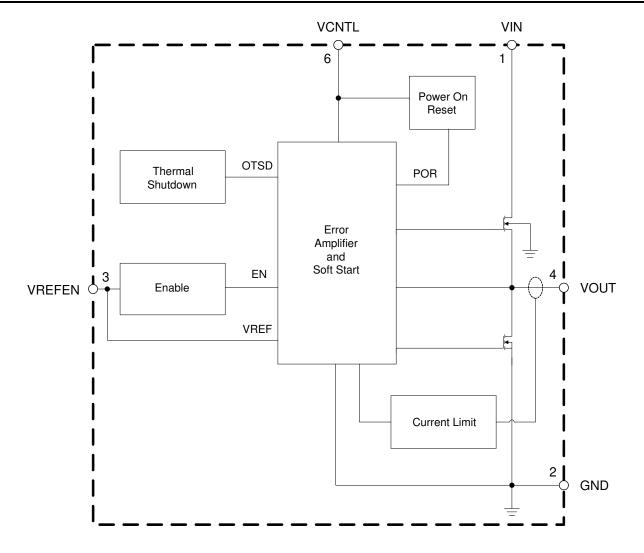




Pin Descriptions

Pin Number	Pin Name	Function
1	VIN	Unregulated input supply. A small $10\mu F$ MLCC should be connected from this pin to GND.
2	GND	Ground
3	VREFEN	Reference voltage input and active low shutdown control pin. Pulling the pin to ground turns off device by BJT or FET. When it is released, a soft-start will take for about 0.1ms.
4	VOUT	Regulated voltage output. A minimum of 10µF ceramic capacitor to ground is required to assure stability.
5, 7, 8	NC	No Connection
6	VCNTL	VCNTL supplies the internal control circuitry and provides the drive voltage.
_	Exposed Pad	The exposed pad should be connected to ground copper for better heat dissipation performance.

Functional Block Diagram







Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Ra	Rating		
V _{IN}	Power Input Voltage	-0.3	-0.3 to 6		
V _{CNTL}	Control Input Voltage	-0.3	-0.3 to 6		
V _{REFEN}	Reference Input Voltage	-0.3	-0.3 to 6		
T _{STG}	Storage Temperature	150	°C		
TJ	Junction Temperature +150		°C		
T _{LEAD}	Lead Temperature (Soldering, 10sec)	+2	+260		
		PSOP-8	80		
θ_{JA}	Thermal Resistance (Junction to Ambient) (Note 5)	SOIC-8	110	°C/W	
_		PSOP-8	38		
θ _{JC}	Thermal Resistance (Junction to Case)	SOIC-8	50	°C/W	
ESD	ESD (Human Body Model)	ESD (Human Body Model) 2000		v	
ESD	ESD (Machine Model)	2	00	V	

Notes: 4. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

5. θ_{JA} is measured with the component mounted on a 2-Layer FR-4 board with 2.54cm*2.54cm thermal sink pad in free air.

Recommended Operating Conditions

Symbol	Parameter	Min	Мах	Unit
V _{CNTL}	Control Input Voltage (Note 6)	3.0	5.5	V
V _{IN}	Power Input Voltage	1.2	5.5	V
V _{REFEN}	Reference Input Voltage	0.6	V _{CNTL} -2.2	V
TJ	Operating Junction Temperature Range	-40	+125	°C
TA	Operating Ambient Temperature Range	-40	+85	°C

Note 6: Keep $V_{CNTL} \ge V_{IN}$ in operation power on and power off sequences.





Electrical Characteristics (@T_A = +25°C, V_{IN} = 1.8V/1.5V/1.35V/1.2V, V_{CNTL} = 3.3V, V_{REFEN} = 0.9V/0.75V/0.675V/0.6V, C_{IN} = 10 μ F (Ceramic), C_{OUT} = 10 μ F (Ceramic), unless otherwise specified.)

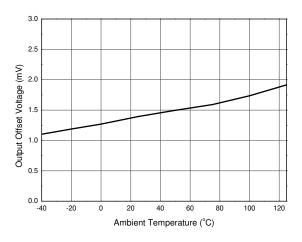
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
Input							
IVCNTL	VCNTL Operating Current	No Load	-	0.5	1.5	mA	
I _{SD-VCNTL}	VCNTL Input Current in Shutdown Mode	V _{REFEN} < 0.15V	-	30	50	μA	
I _{SD-VIN}	VIN Input Current in Shutdown Mode	V _{REFEN} < 0.15V	-1	-	1	μA	
IVREFEN	VREFEN Leakage Current	$V_{\text{REFEN}} = 0.75 V$	-1	_	1	μA	
Output							
V _{OS}	Output Offset Voltage (Note 7)	No Load	-10	0	10	mV	
		$V_{CNTL} = 3.3V$, $I_{OUT} = 1A$	-	220	-		
VDROPOUT	Dropout Voltage	V _{CNTL} = 3.3V, I _{OUT} = 1.5A	-	400	-	mV	
		V _{CNTL} = 3.3V, I _{OUT} = 1.75A	-	520	-	1	
		I _{OUT} = 0A to 1.75A	-20	-20 – 20			
V _{LOAD}	Load Regulation	I _{OUT} = 0A to -1.75A	-20	-	20 mV		
Protection	·						
		Source	1.75	_	-		
I _{LIMIT}	Current Limit	Sink	_	_	-1.75	75 A	
		V _{OUT} = 0V	- 2 -		-		
ISHORT	Short Current	V _{OUT} = V _{IN}	-	-2	-	A	
T _{SHDN}	Thermal Shutdown Temperature	$3.3V \le V_{CNTL} \le 5V$	_	+160	_	°C	
_	Thermal Shutdown Hysteresis	-	_	+30	_	°C	
Start-up & Shutdowr	Function						
VIH		Output = High	0.4	-	-		
V _{IL}	VREFEN Shutdown Threshold Voltage	Output = Low	_	-	0.15	V	
V _{CNTL-ON}		Output = High	2.9	_	_		
V _{CNTL-OFF}	VCNTL Shutdown Threshold Voltage	Output = Low	_	_	2.2	V	
V _{IN-ON}		Output = High 1.1		_	_		
V _{IN-OFF}	VIN Shutdown Threshold Voltage	Output = Low	_	_	0.4	V	

Note 7: V_{OS} is the voltage measurement defined as V_{OUT} subtracted from V_{REFEN} .



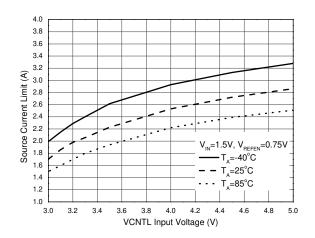


Performance Characteristics

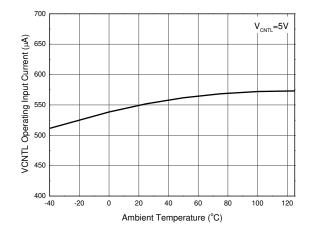


Output Offset Voltage vs. Ambient Temperature

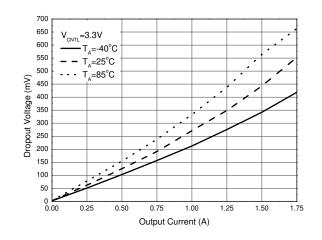
Source Current Limit vs. VCNTL Input Voltage



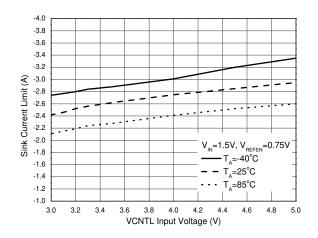
VCNTL Operating Input Current vs. Ambient Temperature



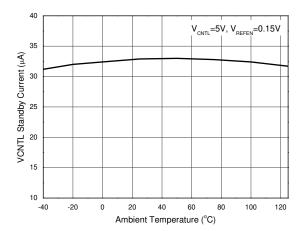
Dropout Voltage vs. Output Current



Sink Current Limit vs. VCNTL Input Voltage



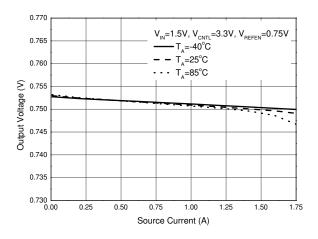
VCNTL Standby Current vs. Ambient Temperature





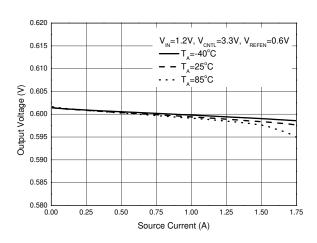


Performance Characteristics (Cont.)

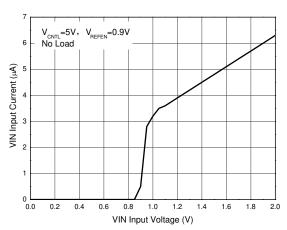


Output Voltage vs. Source Current (DDR-III)

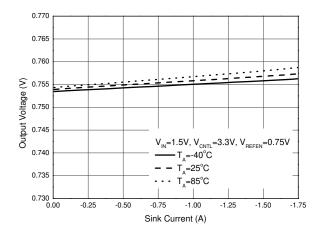
Output Voltage vs. Source Current (DDR-IV)



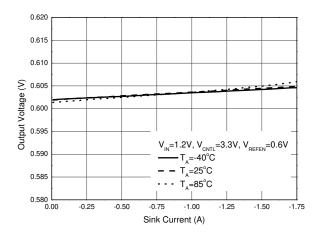
VIN Input Current vs. VIN Input Voltage



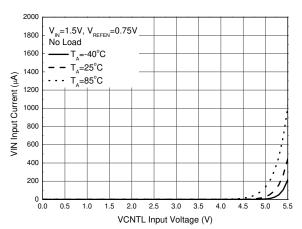
Output Voltage vs. Sink Current (DDR-III)



Output Voltage vs. Sink Current (DDR-IV)



VIN Input Current vs. VCNTL Input Voltage





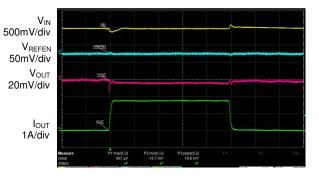


Performance Characteristics (Cont.)



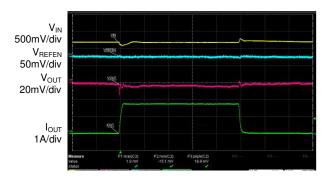
Source Load Transient (DDR-III)

 $(C_{IN}=C_{OUT}=10\mu F, I_{OUT}=0A$ to 1.75Å, $V_{IN}=1.5V, V_{REFEN}=0.75V, V_{CNTL}=3.3V)$



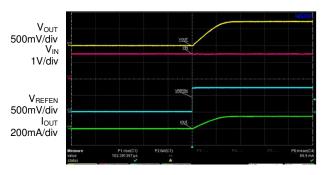
Time 100µs/div

Source Load Transient (DDR-IV) ($C_{IN}=C_{OUT}=10\mu$ F, $I_{OUT}=0$ A to 1.75A, $V_{IN}=1.2$ V, $V_{REFEN}=0.6$ V, $V_{CNTL}=3.3$ V)



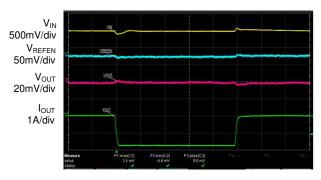
Time 100µs/div

$\label{eq:VREFEN} \begin{array}{l} \text{VREFEN Power On} \\ (C_{\text{IN}} = C_{\text{OUT}} = 10 \mu F, \ R_{\text{LOAD}} = 5 \Omega, \ V_{\text{CNTL}} = 5 V) \end{array}$



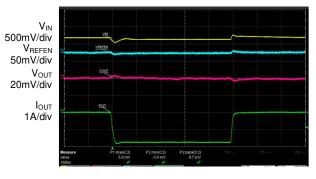
Time 100µs/div

Sink Load Transient (DDR-III) ($C_{IN}=C_{OUT}=10\mu$ F, $I_{OUT}=0$ A to -1.75A, $V_{IN}=1.5$ V, $V_{REFEN}=0.75$ V, $V_{CNTL}=3.3$ V)



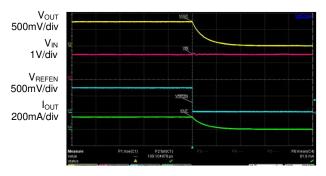
Time 100µs/div

Sink Load Transient (DDR-IV) ($C_{IN}=C_{OUT}=10\mu F$, $I_{OUT}=0A$ to -1.75A, $V_{IN}=1.2V$, $V_{REFEN}=0.6V$, $V_{CNTL}=3.3V$)



Time 100µs/div

 $\label{eq:VREFEN} \begin{array}{l} \text{VREFEN Power Off} \\ (C_{\text{IN}} = C_{\text{OUT}} = 10 \mu F, \ R_{\text{LOAD}} = 5 \Omega, \ V_{\text{CNTL}} = 5 V) \end{array}$

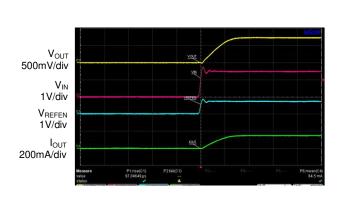


Time $100 \mu s/div$





Performance Characteristics (Cont.)

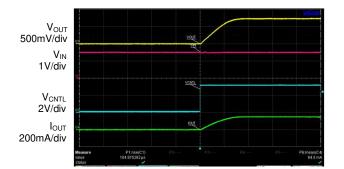


Time 100µs/div

VIN Power On

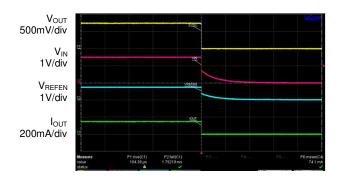
 $(C_{IN}=C_{OUT}=10\mu F, R_{LOAD}=5\Omega, V_{CNTL}=5V)$

$\label{eq:VCNTL Power On} $$ (C_{IN}=C_{OUT}=10 \mu F, R_{LOAD}=5 \Omega) $$$



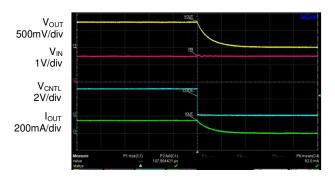
Time 100µs/div

 $\label{eq:VIN Power Off} VIN \ Power \ Off \\ (C_{\text{IN}}=C_{\text{OUT}}=10 \mu F, \ R_{\text{LOAD}}=5 \Omega, \ V_{\text{CNTL}}=5 V)$



Time 500ms/div

 $\label{eq:VCNTL Power Off} $$ (C_{IN}=C_{OUT}=10\mu F, R_{LOAD}=5\Omega)$$$



Time 100µs/div





Application Information

1. Input Capacitor

The input capacitor of VIN should be placed to VIN pin as close as possible. Use a low ESR, 10µF or larger MLCC capacitor to provide surge current during load transient.

The input capacitor for VCNTL is recommended to be 0.47µF or larger to decouple the supply voltage of AP2303's control circuitry.

2. Output Capacitor

The output capacitor is recommended with a 10μ F or higher MLCC capacitor which will be sufficient at full temperature range. An aluminum electrolytic capacitor with low ESR also should be larger than 10μ F. The output capacitor should be placed to VOUT pin as close as possible.

3. Reference Voltage

A reference voltage is applied to the VREFEN pin by a resistor divider between VIN and GND pins. And a 0.1µF to 1µF bypass capacitor is preferred to form a low-pass filter to reduce the noise from VIN. More capacitance and large resistance will increase the start-up time after VIN power-up.

4. Thermal Consideration

There's an internal thermal protection circuitry of AP2303 to protect device during overload conditions. For continuous operation, make sure not to exceed the operating junction temperature range of +125°C. The power dissipation definition in device is:

 $P_{D}=(V_{IN} - V_{OUT})xI_{OUT} + V_{IN}xI_{Q}$

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout and the surrounding airflow. The maximum power dissipation can also be calculated as:

 $\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = (\mathsf{T}_{\mathsf{J}(\mathsf{MAX})}\text{-}\mathsf{T}_{\mathsf{A}})/\theta_{\mathsf{J}\mathsf{A}}$

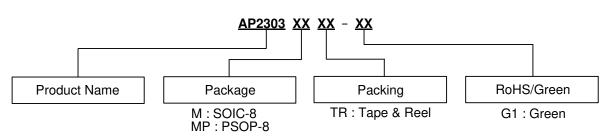
The maximum power dissipation for PSOP-8 package at $T_A = +25^{\circ}C$ can be calculated as:

 $P_{D(MAX)} = (125^{\circ}C-25^{\circ}C) / (80^{\circ}C/W) = 1.25W$





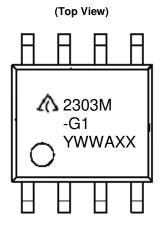
Ordering Information



Package	Temperature Range	Part Number	Marking ID	Packing	
SOIC-8	10.1 07.0	AP2303MTR-G1	2303M-G1	4000/Tape & Reel	
PSOP-8	-40 to +85°C	AP2303MPTR-G1	2303MP-G1	4000/Tape & Reel	

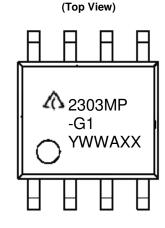
Marking Information

(1) SOIC-8



First and Second Lines: Logo and Marking ID Third Line: Date Code Y: Year WW: Work Week of Molding A: Assembly House Code XX: 7th and8th Digits of Batch No.

(2) PSOP-8



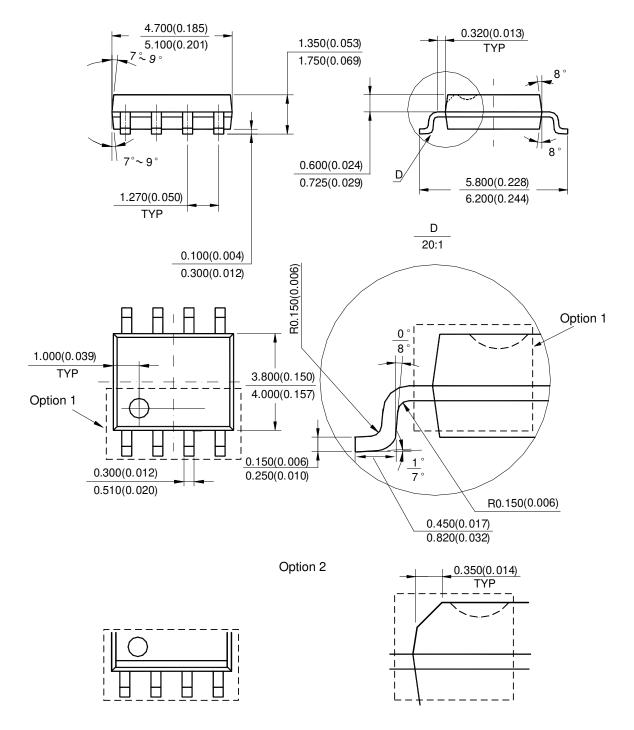
First and Second Lines: Logo and Marking ID Third Line: Date Code Y: Year WW: Work Week of Molding A: Assembly House Code XX: 7th and 8th Digits of Batch No.





Package Outline Dimensions (All dimensions in mm(inch).)

(1) Package Type: SOIC-8



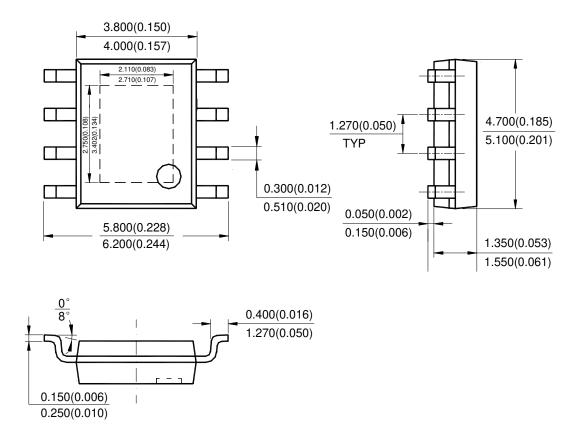
Note: Eject hole, oriented hole and mold mark is optional.





Package Outline Dimensions (Cont. All dimensions in mm(inch).)

(2) Package Type: PSOP-8



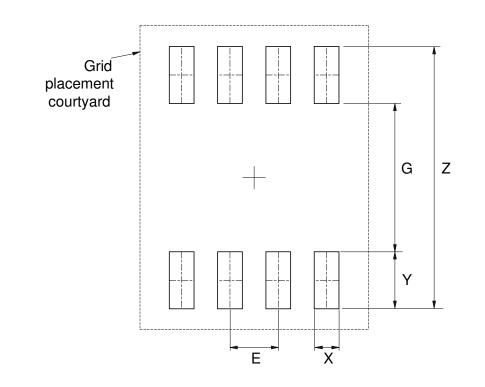
Note: Eject hole, oriented hole and mold mark is optional.





Suggested Pad Layout

(1) Package Type: SOIC-8



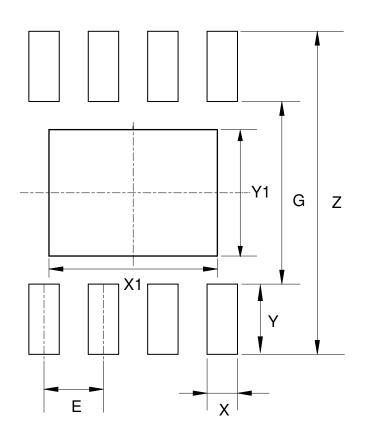
Dimensions	Z	G	Х	Y	E
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	1.270/0.050





Suggested Pad Layout (Cont.)

(2) Package Type: PSOP-8



Dimensions	Z	G	Х	Y	X1	Y1	E
	(mm)/(inch)						
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	3.600/0.142	2.700/0.106	1.270/0.050





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